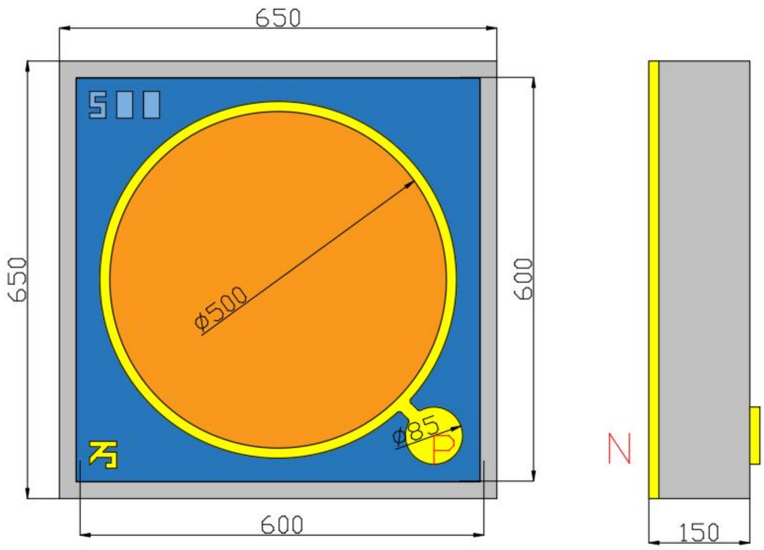
# 1740nm InGaAs 500um PD Chip datasheet

P/N : WIR3-500



## Feature

High responsivity

Low dark current

900-1740nm Spectral range

## Structure

InGaAs / InP PIN Chip.

P Electrode (anode) : Gold.

N Electrode (cathode) : Gold.

## DIMENSIONS

| Conditions | Min. | Typ. | Max | Unit |
|---|---|---|---|---|
| Active | 498 | 500 | 502 | µm |
| Chip width | 630 | 650 | 670 | µm |
| Chip length | 630 | 650 | 670 | µm |
| Chip height | 130 | 150 | 170 | µm |
| Pad Area | 80 | 85 | 90 | µm |

## Electro-Optical Characteristics ( @ Ta=25 ℃)

| Parameter | Symbol | Test Condition | Min. | Typ. | Max. | Unit |
|---|---|---|---|---|---|---|
| Dark current | Id | Vr=-5V | - | 0.2 | 1 | nA |
| Capacitance | Cp | Vr=-5V | - | 15 | 25 | pF |
| Responsivity | R | @1654 nm | 0.9 | 1 | - | A/W |
| Wavelength range | λ | | 900 | 1650 | 1740 | nm |

PS. ESD ( HBM ) > 800V

## ABSOLUTE MAXIMUM RATING

| Parameter | Rating |
|---|---|
| Operating Temperature | -40℃ to 85℃ |
| Storage Temperature | -55℃ to 125℃ |
| Forward Current | 10mA |

---

WinG CHiP 武汉万赢半导体科技有限公司
WUHAN WING CHIP SEMICONDUCTOR TECHNOLOGY Co., LTD.